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AgFeS₂ Nanowires Modified BiVO₄ Photoanode for Photoelectrochemical Water Splitting

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Abstract

Photoelectrochemical water splitting is a very promising and environmentally friendly route for the conversion of solar energy into hydrogen. However, the solar-to-hydrogen conversion efficiency is still very low due to limited light absorption and rapid bulk recombination of charge carriers. In this work, we present a novel ternary sensitizer AgFeS₂, with a narrow band gap of 0.9 eV, combined with BiVO₄ to enhance the solar-to-hydrogen energy conversion efficiency. The photoelectrochemical properties of AgFeS₂/BiVO₄ electrode are investigated and the photocurrent densities of AgFeS₂/BiVO₄ composite electrodes are greatly enhanced compared with pristine BiVO₄ (15 times higher at 0.6 V vs. Ag/AgCl under AM 1.5 G illumination). The enhanced photoelectrochemical properties stem from the extended light absorption spectrum, fast charge transfer and appropriate energy gap alignment. It is demonstrated that AgFeS₂ nanowire is a promising inorganic sensitizer for improving the solar water splitting efficiency.

1. Introduction

Since the discovery of water splitting on titanium dioxide (TiO_2) surface by photoirradiation, photoelectrochemical (PEC) technology has attracted extensive interest.^[1] After decades of development, it has made great progress in the H_2 production of water splitting, degradation of organic pollutants and CO_2 reduction.^[2-5] However, the PEC efficiency is still low, seriously restricting its wide application in solving the energy shortage and environmental pollution problems. Exploring new and efficient photoelectrodes is proved to be an important strategy for improving PEC efficiency and promoting the practical application of PEC technology. Among photoelectrode materials, bismuth vanadate (BiVO_4) is one of the leading metal oxides, with a direct bandgap of 2.3~2.4 eV and a suitable valence band position for O_2 evolution.^[6] BiVO_4 was first reported by Kudo and coworkers as a photocatalyst for water oxidation.^[7] Since then BiVO_4 has been widely investigated as a visible-light-driven photocatalyst for water oxidation and organic compound degradation.^[8-12] Recently, extensive attention has focused on BiVO_4 as a photoanode for PEC water splitting.^[13-16] However, the activity of pure BiVO_4 is low due to its poor light absorptive performance and difficult migration of electron-hole pairs, which has been demonstrated by van de Krol and coworkers.^[17] Therefore, poor electron transport results in high bulk recombination of photogenerated charge carriers and a low solar-to-hydrogen conversion efficiency.

To address these issues, many attempts have been made to modify the bulk electronic properties of BiVO_4 photocatalysts, such as noble metals coating, elemental doping and narrow bandgap semiconductors combining.^[15, 18-23] Among these methods, one of the most efficient ways is to deposit a sensitizer with appropriate band gap on BiVO_4 . The sensitizer not only extends the light absorption spectrum, but also accelerates photogenerated electron-hole separation. Ternary I-III-VI₂ semiconductors have been regarded as one of the most promising materials for thin film sensitizer because of their unique properties, large absorption coefficients, high conversion efficiency, and low toxicity.^[24] Silver iron sulfide

(AgFeS₂, Lenaite) is a novel ternary I-III-VI₂ semiconductor, which has a narrow band gap (about 0.9 eV) covering the entire visible spectrum and also has a high absorption coefficient. ^[25] Han et al. and Sciacca et al. successfully obtained AgFeS₂ via different synthetic pathways. ^[25, 26] To the best of our knowledge, there has been no report on PEC electrode made from BiVO₄ modified with ternary AgFeS₂ so far. This study extends the work to a new coupled photoanode made of ternary sensitizer AgFeS₂ and BiVO₄.

We have successfully prepared the AgFeS₂/BiVO₄ composite by incorporating AgFeS₂ with BiVO₄ film via a simple drop-coating method. The composite of AgFeS₂ and BiVO₄ semiconductors with appropriate oxidation reduction energy levels can enhance the charge separation and engender its wide spectral response by extension of light absorption in the visible region. In this study, ternary AgFeS₂ sensitizer modified BiVO₄ is fabricated on fluorine-tin-oxide (FTO) substrate and applied as photoanode. The expected enhanced PEC properties of AgFeS₂/BiVO₄ composite is confirmed by hydrogen and oxygen evolution from solar water splitting. The mechanism for the enhanced PEC performance and gas evolution on AgFeS₂/BiVO₄ composite is discussed in detail.

2. Results and Discussion

2.1. Fabrication and Characterization of AgFeS₂/BiVO₄ Composite Electrodes

Scanning electron microscope (SEM) is employed to investigate the morphology of the as-prepared AgFeS₂, BiVO₄ and AgFeS₂/BiVO₄ samples (**Figure 1**). Figure 1a shows the typical morphology of AgFeS₂. It is comprised of nanowires, and the length is about ten micrometers. Meanwhile, the morphology of the BiVO₄ (Figure S1, Supporting information) is also investigated, which is comprised of nanoparticles with diameter from 100 to 400 nm. Herein, AgFeS₂ nanowires are firstly prepared via a solution phase conversion of metallic Ag nanowires from our previous report. ^[25] The as-prepared AgFeS₂ nanowires are then stirred in ethanol for 24 hrs to form suspension, which are dropped onto the BiVO₄ film to obtain

AgFeS₂/BiVO₄ composites. According to the amount of AgFeS₂ (10, 20, 30, 40 and 50 μ L) being added on the BiVO₄ samples, the corresponding AgFeS₂/BiVO₄ samples are labeled as AB-10, AB-20, AB-30, AB-40 and AB-50, respectively. As the morphologies of AgFeS₂/BiVO₄ samples with different amount of AgFeS₂ are almost the same, only the coverage of AgFeS₂ on BiVO₄ is different. While the photocurrent density of AB-40 electrode is higher than other AgFeS₂/BiVO₄ samples, it is thus chosen as the example for the SEM and energy-dispersive X-ray (EDX) measurements. In the AB-40 sample, it is clearly observed that AgFeS₂ nanowires are on the top surface of BiVO₄ (Figure 1b and S2). Additionally, EDX mapping obtained in SEM mode (**Figure 2**) is performed to confirm the composition of AB-40. As seen from the SEM image (Figure 2a), AgFeS₂ nanowires are nanocrystalline, which is confirmed by electron diffraction in our previous synthetic study.^[25] Moreover, the Ag, Fe, and S elements (Figure 2b-d) are distributed homogeneously along the nanowires, indicating the existence of AgFeS₂. Bi, V and O (Figure 2e-g) elements are also detected, which come from the BiVO₄ substrate. The composite structure of AgFeS₂/BiVO₄ is thus confirmed by the SEM and EDX studies.

The crystal structure of BiVO₄ and AB-40 are determined by XRD, as shown in **Figure 3**. The XRD pattern of BiVO₄ can be matched to monoclinic BiVO₄ (JCPDS No. 14-0688), and the FTO film (JCPDS No. 41-1445) is shown in Figure S3. The 2 θ diffraction peaks of 28.8°, 30.5°, 34.5°, 35.2°, 39.8° and 42.5° can be respectively indexed as (121), (040), (200), (002), (211), and (051) planes of monoclinic BiVO₄ structure, which is consistent with the literature.^[27] Moreover, the 2 θ diffraction peaks and corresponding planes of AgFeS₂ (JCPDS No. 48-1895) are shown in Figure S4. It is noteworthy that AgFeS₂ is clearly observed in the XRD pattern of the AB-40 sample. Based on the results of SEM images, elemental mapping and XRD patterns, it is clear that the AgFeS₂/BiVO₄ composite is successfully prepared via a simple drop-coating approach.

It is well known that light absorption of the photoelectrode materials plays an important role in the solar water splitting. The UV–vis diffuse reflection spectra of BiVO₄, AgFeS₂, and AgFeS₂/BiVO₄ composites with different AgFeS₂ contents are thus studied. The optical band gap energy (E_g) of BiVO₄ (Figure S5) is obtained by using the equation of $(F(R) E)^{1/2} = A (E - E_g)$.^[28] The estimated band gap value of BiVO₄ as a direct band semiconductor is 2.32 eV, which is in agreement with the previous reports.^[7, 8] To further analyze the diffuse reflection spectra of AgFeS₂/BiVO₄ composites (**Figure 4**), it can be found that there are obvious enhancements in the light absorption of AgFeS₂/BiVO₄ composites, compared with the bare BiVO₄. This is due to the fact that AgFeS₂ with its narrow band gap (0.88 eV) significantly extends the light absorption range of AgFeS₂/BiVO₄ composites. With the introduction of AgFeS₂, a more efficient utilization of the solar spectrum on AgFeS₂/BiVO₄ can be achieved, which is helpful to improve the PEC properties and facilitates its use in practical solar water splitting. The AgFeS₂/FTO film is prepared by adding AgFeS₂ suspension onto FTO until it is fully covered with AgFeS₂ sample. Therefore, the amount of AgFeS₂ on the FTO substrate is higher than the other samples, this is the reason that AgFeS₂ film has much lower %R.

2.2. Photoelectrochemical Properties of AgFeS₂/BiVO₄ Electrodes

Photocurrent densities as a function of applied potential of AgFeS₂, BiVO₄ and AgFeS₂/BiVO₄ electrodes are investigated by linear sweep photovoltammetry (LSV), which demonstrates the electron generation capacity and electron transfer effectiveness. The photocurrent responses of AgFeS₂, BiVO₄ and AgFeS₂/BiVO₄ photoelectrodes (**Figure 5**) are studied under AM 1.5G illumination (100 mW/cm²). Figure 5a shows the LSV (scan rate: 10 mV/s) on the BiVO₄, AgFeS₂ and AgFeS₂/BiVO₄ photoanodes under light illumination from the backside (FTO side) of the electrodes. The anodic photocurrents increase steadily with the applied positive potential, and an enhanced photocurrent for the AgFeS₂/BiVO₄ composite electrodes is obtained essentially over the entire potential range compared with BiVO₄ electrode. The AB-40 electrode shows the maximum enhancement among all of the electrodes,

and the current in the dark is negligible. This significant improvement in photocurrent could be attributed to the effect of AgFeS₂ modification. It is also notable that pristine AgFeS₂ shows a very low photocurrent. The LSVs of the photoanodes under chopped illumination are also studied and shown a similar trend in Figure 5b. Herein, the BiVO₄ photoanode demonstrates low photocurrent, which is largely lower than most of the previous reports in the literature on BiVO₄ photoelectrodes.^[29, 30] The poor PEC performance is mainly caused by non-uniform distribution of the BiVO₄ nanoparticles on the FTO surface, which is not fully covered by BiVO₄ nanoparticles. It is thus anticipated that the photocurrent of AgFeS₂/BiVO₄ composite would be much higher if BiVO₄ substrate with better quality is employed.

Additional photoelectrochemical measurements (**Figure 6**) are performed to further investigate the enhancement mechanism for water splitting of AgFeS₂/BiVO₄ composite electrode. Figure 6a shows the photocurrent versus time curves (0.6 V vs. Ag/AgCl under AM 1.5 G illumination) for the samples with several on-off cycles. The photocurrent responses of the AgFeS₂/BiVO₄ composite films are higher than that of BiVO₄ and AgFeS₂, and AB-40 possesses the highest photocurrent among them, which is almost 15 times higher than that of BiVO₄. As shown in Figure 6b, it is clearly shown that the radius of the arc on the electrochemical impedance spectroscopy (EIS) Nyquist plots of AgFeS₂/BiVO₄ samples are smaller than that of the BiVO₄, which reflect that AgFeS₂/BiVO₄ possessed faster interfacial charge transfer. The results are in good agreement with the photocurrent measurements. According to the photocurrent graphs and EIS plots, it indicates that the presence of AgFeS₂ in the AgFeS₂/BiVO₄ composite is capable of improving separation efficiency and effectively inhibiting the recombination of photogenerated electron-hole pairs. Such an explanation would also make more sense given its small bandgap, which means it shouldn't participate directly in water splitting.

To further gain a qualitative understanding of the charge recombination behavior in BiVO₄ and AB-40, the transient photocurrent decay occurring immediately upon illumination is

investigated (Figure 6c). Transient photocurrent response has been demonstrated to be a useful technique for investigating the efficiency of the separation of photogenerated electron–hole pairs.^[31] The photocurrent curve initially presents a spike and then the spike gradually decays until the photocurrent reaches a stable value. The decrease in the photocurrent indicates that recombination is occurring within the AgFeS₂/BiVO₄ electrode. When the light is switched on, a photocurrent spike is observed at an applied potential of 0.6 V vs. Ag/AgCl due to the sudden generation of charge carriers, which then recombine after generation. Charge recombination can be caused either by accumulation of electrons in the bulk or accumulation of holes at the surface. The accumulation of holes would cause an equally large cathodic transient when the light is switched off and electrons in the conduction band react with the accumulated holes.^[9] However, cathodic transients can barely be observed, indicating accumulation of holes are not the main recombination process in BiVO₄ film and AB-40 electrodes. The transients in Figure 6c are thus attributed to the accumulation of electrons due to the poor electron transportation in BiVO₄, which is consistent with the results observed in the previous reports.^[14] The transient decay time can be calculated from a logarithmic plot of parameter D , given by the equation^[32, 33]:

$$D = (I_t - I_s) / (I_m - I_s) \quad (1)$$

where I_m is the photocurrent spike, I_t is the photocurrent at time t and I_s is the steady state photocurrent. I_s is achieved as the recombination and charge generation reaches equilibrium. The transient decay time is defined as the time at which $\ln D = -1$.^[32] Therefore, based on the photocurrent profiles measured in Figure 6c, the transient decay times of BiVO₄ film and AB-40 electrodes are calculated and plotted in Figure 6d. The transient decay time for AB-40 electrode is 1.87 s, which is more than three times longer than the transient decay time of BiVO₄ film (0.49 s). Generally, the photocurrent decay rate is determined by charge carrier recombination rate.^[33] Therefore, we expect that a slower recombination rate gives rise to a longer transient decay time and a significantly longer transient decay time is observed for the

AB-40, suggesting a lower charge carrier recombination rate in the AB-40 compared to the BiVO₄ film.

In order to address the quantitative correlation between AgFeS₂ sensitization and light absorption of AgFeS₂/BiVO₄ composite, incident-photon-to-current-conversion efficiency (IPCE) measurements are performed to study the photoactive wavelength regime for AgFeS₂, BiVO₄ and AB-40 (**Figure 7**). IPCE can be expressed as: ^[34, 35]

$$\text{IPCE} = (1240 \times I) / (\lambda \times J_{\text{light}}) \quad (2)$$

where I is the photocurrent density, λ is the incident light wavelength, and J_{light} is the measured irradiance. For AgFeS₂ itself, the IPCE data is very low, which is consistent with the photocurrent data. The IPCE plots of BiVO₄ and AB-40 look similar and strongly decrease upon excitation at longer wavelengths, the BiVO₄ shows a minimal photoresponse below the bandgap energy (~2.32 eV, 535 nm), while the composite electrode (AB-40) shows a significant red shift toward lower energy. For example, at above-bandgap illumination, the IPCE of pure BiVO₄ and AB-40 samples at the incident wavelength of 500 nm are 1.03% and 6.59%, indicating the presence of AgFeS₂ can improve the charge separation efficiency and thus an enhanced photoresponse. At below bandgap illumination of 550 nm, the IPCE of AB-40 is around 5%, while pristine BiVO₄ shows no photoresponse. This is the direct evidence that AgFeS₂ can also act as a photosensitizer and substantially improves the light collection and conversion efficiency in the visible region.

To verify that the measured photocurrent of the photoanodes originated from water splitting rather than any other undesired side reactions, a water splitting experiment is performed at 1.6 V on the AB-40 photoanode, and the gas evolution (**Figure 8**) and corresponding photocurrent response (Figure S6) are measured. The ratio of evolution rates of H₂ and O₂ is close to the stoichiometric value of 2.0, with rates of $9.1 \pm 0.1 \mu\text{mol h}^{-1} \text{cm}^{-2}$ for H₂ and $4.3 \pm 0.1 \mu\text{mol h}^{-1} \text{cm}^{-2}$ for O₂. Assuming 100% Faradaic efficiency, at a photocurrent of 0.60 mA cm⁻², the evolution rates of H₂ and O₂ should be $10.6 \mu\text{mol h}^{-1} \text{cm}^{-2}$ and $5.3 \mu\text{mol h}^{-1} \text{cm}^{-2}$,

respectively. Hence the faradaic efficiencies for H₂ and O₂ are more than 80%, indicating that the observed photocurrent could be mostly attributed to water splitting. Additionally, the photocurrent of AB-40 only very slightly decreases after 3 hrs of water splitting experiment (Figure S6), implying the high stability of the AgFeS₂/BiVO₄ composite photoanode. It can be concluded that AgFeS₂ is relatively stable and promising as a sensitizer for solar water splitting.

2.3. Photoelectrochemical Mechanism for the Water Splitting over AgFeS₂/BiVO₄ Composite Photoanode

Based on the above data, a possible mechanism for the water splitting over AgFeS₂/BiVO₄ composite photoanode under light irradiation can be proposed. Here AgFeS₂ serves as a sensitizer for light-induced redox process while BiVO₄ is a substrate. The band gap of BiVO₄ is evaluated as 2.32 eV from the UV-vis spectrum, which is consistent with literature reports. The corresponding conduction band (E_{CB}) and valence band positions (E_{VB}) of BiVO₄ and AgFeS₂ at the point of zero charge are presumed through the following equations^[36, 37]:

$$\chi = 1/2(A_f + I_1) \quad (3)$$

$$E_{CB} = \chi - E_0 - 1/2E_g \quad (4)$$

where χ is the bulk electronegativity of the compound, defined as the arithmetic mean of the atomic electron affinity and the first ionization energy (for BiVO₄, χ is 6.04 eV^[37, 38]; for AgFeS₂, χ is 5.14 eV^[36]). E_0 is the energy of free electrons on the hydrogen scale (about 4.5 eV), and E_g is the band gap energy of the semiconductor. The position of the valence band edge is determined by $E_{VB} = E_{CB} + E_g$. The calculated result shows that the bottom of the conduction band of BiVO₄ is around 0.4 eV versus normal hydrogen electrode (NHE), while the top of the valence band is around 2.7 eV. Meanwhile, the value of E_{CB} measured (Figure S7) by photocurrent onset potential is accorded with the calculated result. The calculated conduction band and valence band positions (vs. NHE) of AgFeS₂ and BiVO₄ are listed in

Table 1.

The energy band diagram of the AgFeS₂/BiVO₄ composite photoanode is presented in **Figure 9**. The difference in E_{CB} between AgFeS₂ and BiVO₄ allows for the transfer of electrons from the conduction band of AgFeS₂ to that of BiVO₄. Upon light irradiation ($\lambda < 535$ nm), both the AgFeS₂ and BiVO₄ components generate electron-hole pairs, although the majority from the BiVO₄ due to its large excess. Whereas the electrons are able to move easily to the FTO contact, the holes are expected to be left on the surface of AgFeS₂/BiVO₄ photoanode. This improved charge separation efficiency leads to the improved water oxidation. On the other hand, under light irradiation beyond the absorption edge of BiVO₄ ($\lambda > 535$ nm), the electrons photogenerated in AgFeS₂ due to its small band gap can readily transfer to the conduction band of BiVO₄, which improves the charge carrier separation in AgFeS₂. AgFeS₂ itself is unable to directly split water toward O₂ due to the unfavorable position of valence band with respect to the O₂/H₂O redox potential. However, the holes trapped at the AgFeS₂ component can react with H₂O to form OH radicals ($\text{H}_2\text{O} + \text{h}^+ \rightarrow \text{OH}^\bullet + \text{H}^+$).^[39] OH radicals are highly reactive and, in absence of other species, can couple with another OH radical to form H₂O₂ ($2\text{OH}^\bullet \rightarrow \text{H}_2\text{O}_2$).^[40] Hydrogen peroxide is known to decompose spontaneously to O₂ and water, and H₂O₂ can also be photo-oxidized by holes in BiVO₄ ($\text{H}_2\text{O}_2 + \text{h}^+ \rightarrow \text{O}_2 + \text{H}^+ + 4\text{e}^-$).^[41-43] In conclusion, photogenerated holes formed in both BiVO₄ and AgFeS₂, following different pathways, can react with water to form O₂ which results in higher number of collected photoelectrons,^[44, 45] then used for the H₂ production in the cathodic electrode.

4. Conclusions

AgFeS₂ nanowire/BiVO₄ composite photoelectrodes are fabricated via a facile drop-coating method. AgFeS₂ nanowire, with a narrow band gap of 0.9 eV, as a novel ternary sensitizer to improve the water splitting efficiency of BiVO₄ photoanode is demonstrated. The photocurrent density of AgFeS₂/BiVO₄ electrode is greatly enhanced compared with pristine

BiVO₄ electrode (15 times higher at 0.6 V vs. Ag/AgCl under AM 1.5 G illumination). The excellent photoelectrochemical properties stem from the extended light absorption spectrum and improved charge separation and collection efficiency. Furthermore, hydrogen and oxygen production on AgFeS₂/BiVO₄ electrodes is measured and these composite photoelectrodes are found to be promising for solar water splitting. AgFeS₂ drastically improves the solar water splitting efficiency of BiVO₄ photoanodes, suggesting AgFeS₂ as a new effective sensitizer for improving the efficiency of solar-to-fuel energy conversion. Further work on preparing more active BiVO₄ substrate and more stable AgFeS₂ by surface modification is being carried out in our lab.

4. Experimental section

Preparation of the AgFeS₂/BiVO₄ composite: The AgFeS₂ nanowires were obtained using a modified synthesis from our previous report, optimized further for larger scale reactions with higher yield.^[25] In a typical reaction, 90 mL of DMSO was placed in a round bottom flask. 102 mg of FeCl₂·4H₂O, 100 μL of thioglycolic acid and 2.5 mL of 20 g/L Ag nanowire solution were added to the DMSO. N₂ was bubbled for 30 min to remove oxygen. Subsequently, 10 mL of water with 451 mg of Na₂S₂O₃·5H₂O purged with N₂ was slowly added to the rest of the reagents, and this step took approximately 30 min. The color of the solution was dark purple at this stage. The round bottom flask was then placed in an oil bath at 150 °C and refluxed for 90 minutes. After 90 min, the solution was allowed to cool to room temperature, centrifuged several times at 3000 rpm for 5 minutes and then washed in water and ethanol to remove DMSO and any unreacted species.

In the BiVO₄ synthetic procedure, Bi (NO₃)₃·5H₂O (0.5 mmol) and NH₄VO₃ (0.5 mmol) were dissolved in 5 mL of nitric acid and 5 mL of distilled water. The mixed solution (20 μL) was dropped twice onto the FTO surface with 1 cm × 1 cm area. After being dried, the film was calcined at 500 °C for 2 h with the ramping rate of 2 °C/ min.

The AgFeS₂/BiVO₄ composites were prepared via dropping the AgFeS₂ suspension onto the BiVO₄ film. Firstly, 4 mg AgFeS₂ was added into 200 μ L ethanol with constant stirring. After being stirred for 24 hrs, the AgFeS₂ suspension was dropped onto the BiVO₄ film. The amount of AgFeS₂ addition were 10, 20, 30, 40 and 50 μ L, and the corresponding AgFeS₂/BiVO₄ samples were labeled as AB-10, AB-20, AB-30, AB-40 and AB-50, respectively. The AgFeS₂/FTO film was prepared by adding AgFeS₂ suspension onto FTO film until it was fully covered with AgFeS₂ sample.

Characterization of samples: The X-ray diffraction (XRD) patterns were measured by a Bruker D8 Advance X-ray diffractometer with Cu K radiation. The accelerating voltage and applied current were 40 kV and 40 mA, respectively. UV-vis diffuse reflectance spectra of samples were collected by an UV-vis-NIR spectrometer (UV-2600, Shimadzu co., Japan) with BaSO₄ as the background and in the range 200–800 nm. The general morphologies and element mapping of the products were examined by field emission scanning electron microscopy (FESEM) on a Sigma Zeiss 150 (Carl Zeiss Co., Germany) instrument operated at 5 kV. The photoelectrochemical data was collected by a CHI-660E electrochemical workstation (Chenhua Instruments, Co., Shanghai). The photoelectrochemical experiment was carried out in a conventional three-electrode system with a quartz cell. A platinum wire and an Ag/AgCl electrode were used as the counter and reference electrodes, respectively. The electrolyte was 0.1 M Na₂SO₄ solution.

Photoelectrochemical Measurement: The photoelectrochemical characterization was performed with the CHI-660E electrochemical workstation under illumination by a 300 W Xe lamp (CEL-S500, Beijing Jin Yuan science and Technology Co., China) equipped with the AM 1.5G filter (light intensity: 100 mW/cm²). The incident-photon-to-current-conversion efficiency (IPCE) was measured by interposing a monochromator (7ISW15, Beijing 7-Star Optical Instruments Co., China) between the xenon lamp and the photoelectrochemical cell. The monochromatic light was filtered by filter plates for different wavelengths with a

bandwidth of 10 nm, and the monochromatic light power density was measured by a UV-vis irradiatometer (CEL-NP2000, Beijing Jin Yuan science and Technology Co., China) with an accuracy of 1 $\mu\text{W}/\text{cm}^2$.

Supporting Information

Supporting Information is available from the Wiley Online Library or from the author.

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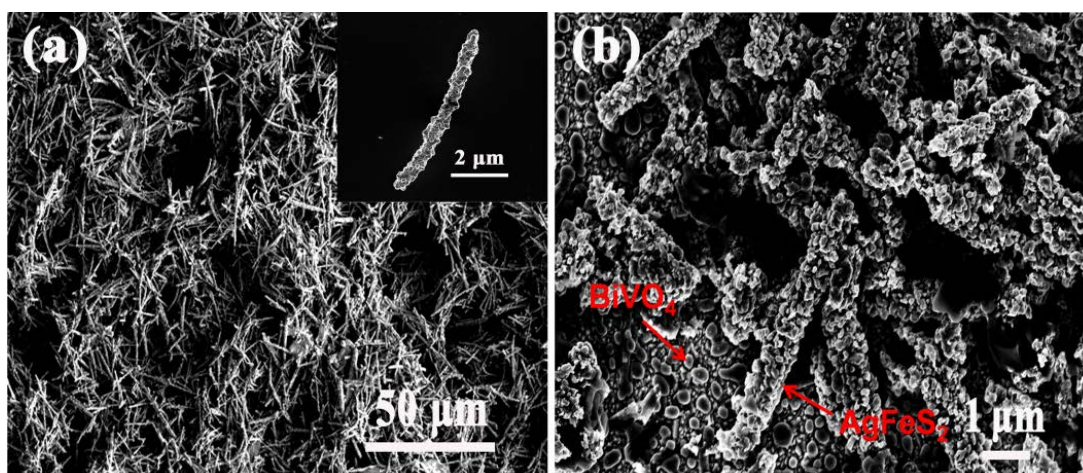


Figure 1. SEM images of AgFeS₂ nanowires (a) and AB-40 composite (b).

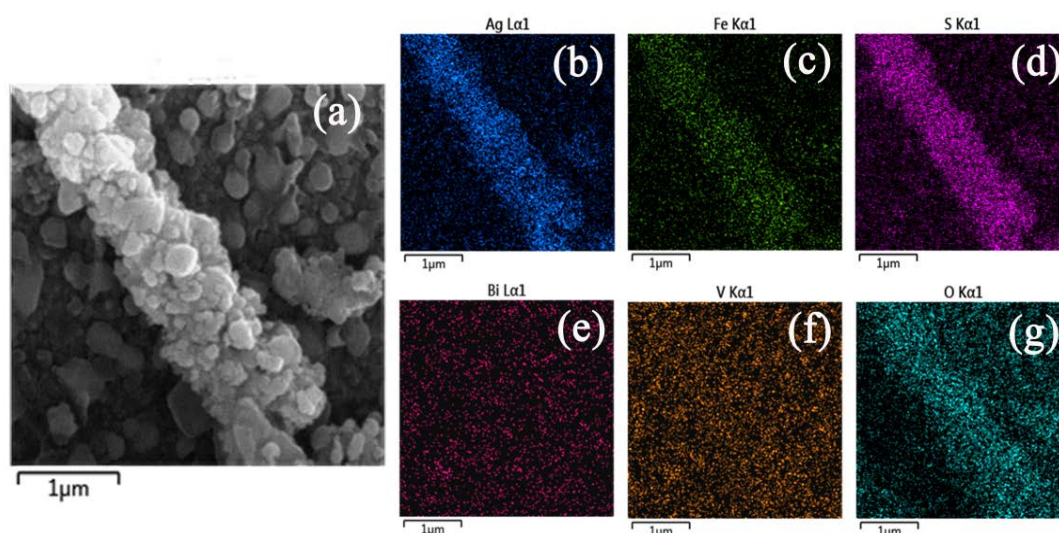


Figure 2. SEM image and EDX characterizations of AB-40 sample: (a) High-magnification SEM image; (b–g) Element mapping of Ag, Fe, S, Bi, V and O, respectively.

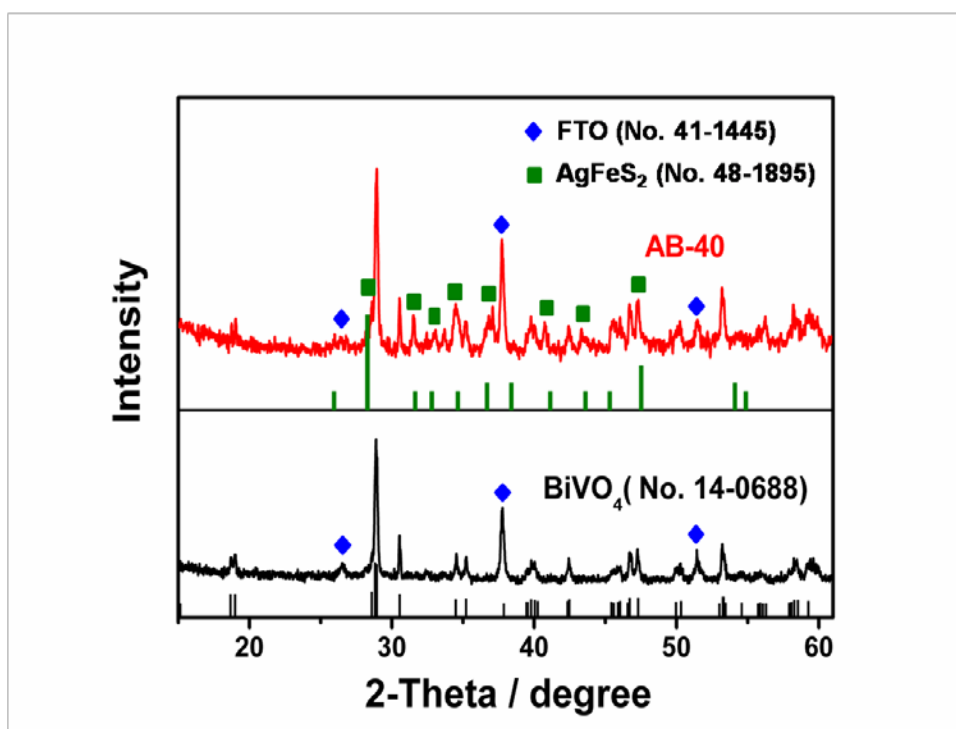


Figure 3. XRD patterns of BiVO_4 and AB-40.

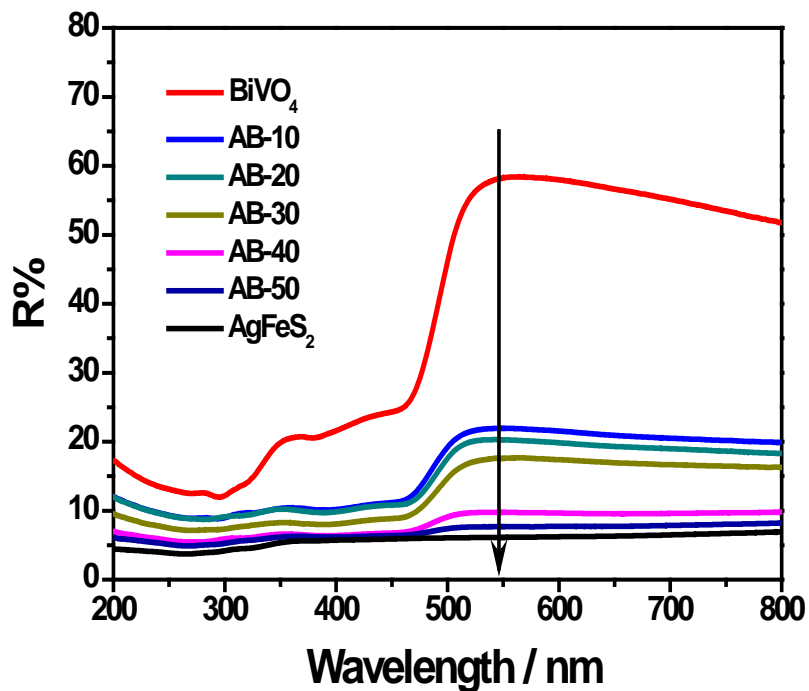


Figure 4. UV-vis diffuse reflectance spectra of AgFeS_2 , BiVO_4 and $\text{AgFeS}_2/\text{BiVO}_4$ composites with different AgFeS_2 contents.

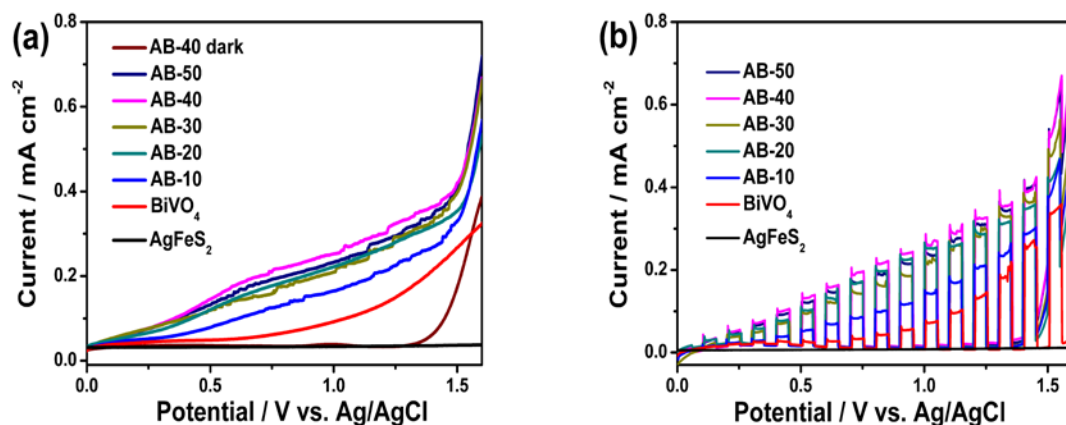


Figure 5. Photocurrent generation versus bias potential (vs. Ag/AgCl) obtained from AgFeS₂, BiVO₄ and AgFeS₂/BiVO₄ composites without being chopped (a) and chopped (b) in 0.1 M Na₂SO₄ under AM 1.5 G illuminations (100 mW/cm²).

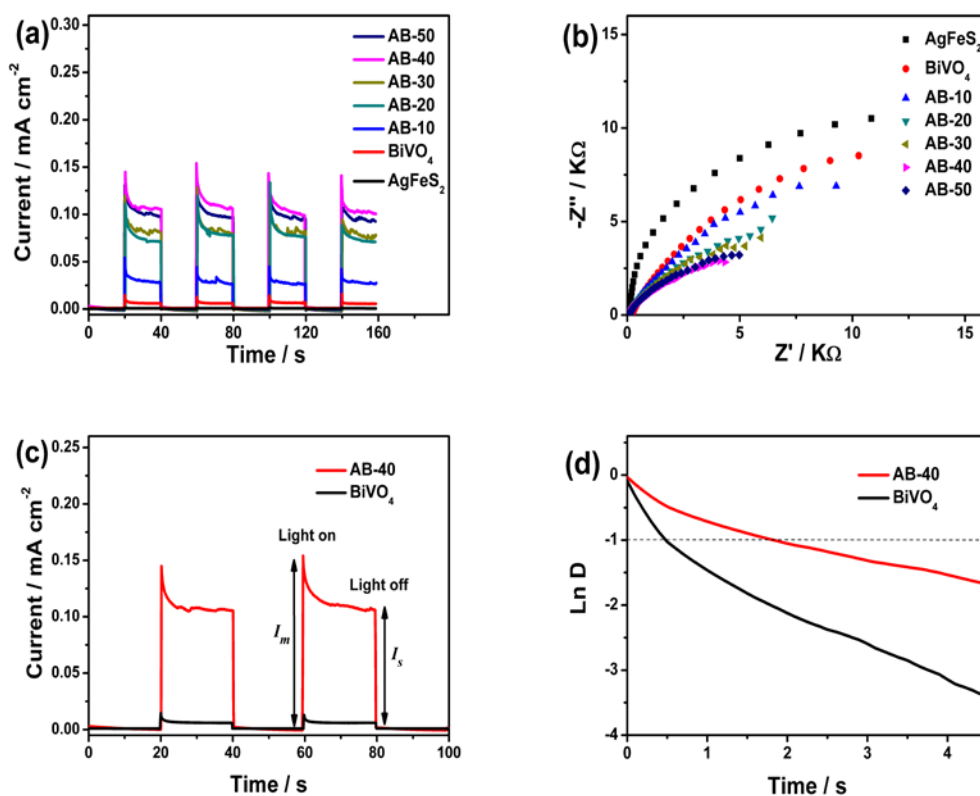


Figure 6. (a) Photocurrent spectra and (b) EIS Nyquist plots of AgFeS₂, BiVO₄ and AgFeS₂/BiVO₄ with an applied bias potential of 0.6 V vs. Ag/AgCl under AM 1.5 G illuminations (100 mW/cm²). (c) Transient photocurrent decay and (d) Transient decay times of BiVO₄ film and AB-40 electrodes (see text for definition of parameter D).

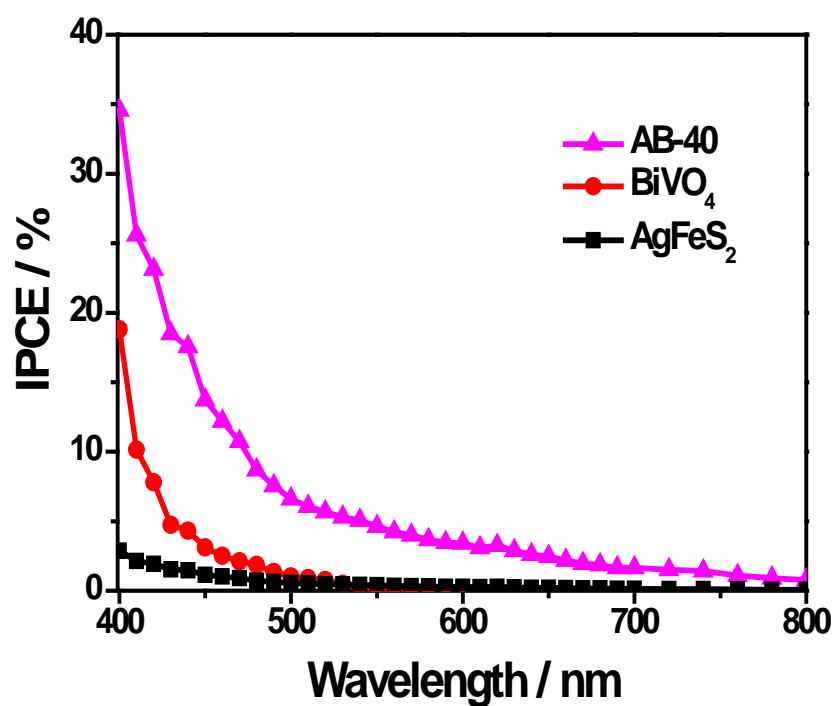


Figure 7. Measured IPCE spectra of AgFeS₂, BiVO₄ and AB-40 in the region of 400 to 800 nm at a potential of +0.6 V under AM 1.5 G illuminations (100 mW/cm²), respectively.

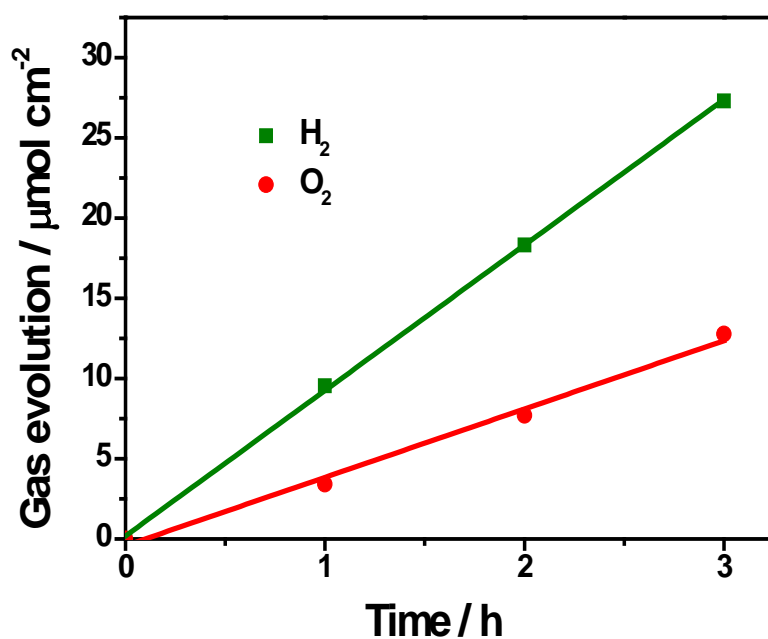


Figure 8. Gas evolution of the AB-40 photoanode at an applied potential of 1.6 V (vs Ag/AgCl) under AM 1.5 G illuminations (100 mW/cm²).

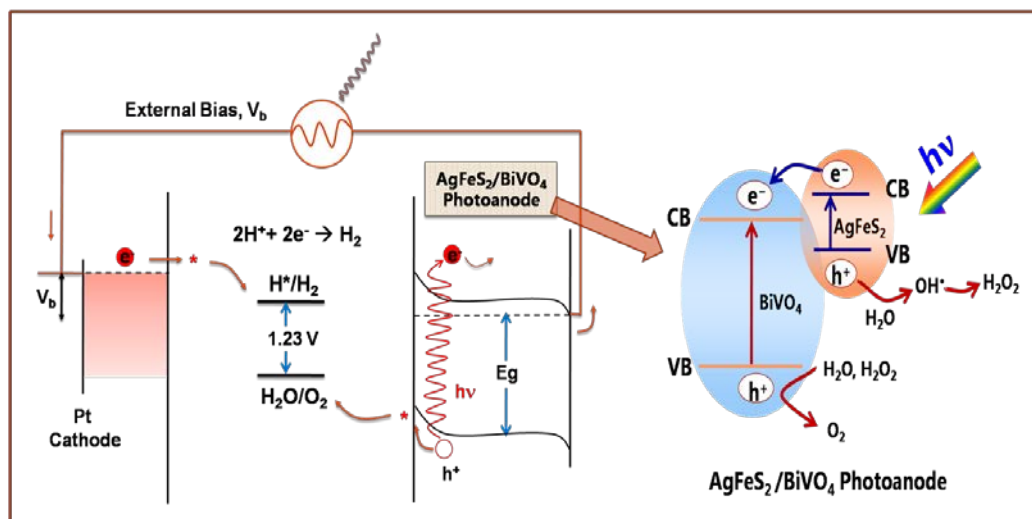


Figure 9. Mechanism of UV-Vis light absorption and charges transfer in $\text{AgFeS}_2/\text{BiVO}_4$ composite films for the photoelectrochemical water splitting reaction.

Table 1. Absolute electronegativity, energy band gap, calculated conduction band and valence band edge versus normal hydrogen electrode (NHE) at the point of zero charge for AgFeS_2 and BiVO_4 semiconductors.

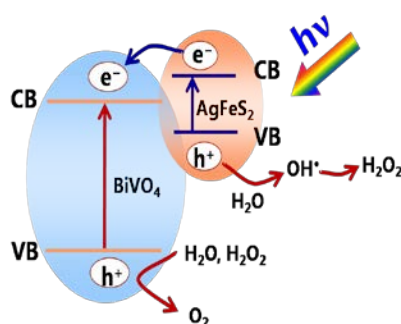
Semiconductor	Absolute electronegativity (χ) (eV)	Calculated conduction band edge (eV)	Calculated valence band edge (eV)	Energy band gap E_g (eV)
AgFeS_2	5.14	0.04	0.92	0.88
BiVO_4	6.04	0.38	2.70	2.32

A novel ternary sensitizer AgFeS_2 is used to optimized BiVO_4 for photoelectrochemical water splitting to enhance the solar-to-hydrogen conversion efficiency. $\text{AgFeS}_2/\text{BiVO}_4$ composite electrode is found to be promising for solar water splitting, which possesses extended light absorption spectrum and improved charge separation and collection efficiency.

ternary sensitizer, extended light absorption, PEC, composite, solar-to-hydrogen

X. Zheng^a, B. Sciacca^b, E. C. Garnett^{b*}, L. Zhang^{a*}

AgFeS_2 Modified BiVO_4 Photoanode for Photoelectrochemical Water Splitting



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Supporting Information

AgFeS₂-Nanowire-Modified BiVO₄ Photoanodes for Photoelectrochemical Water Splitting

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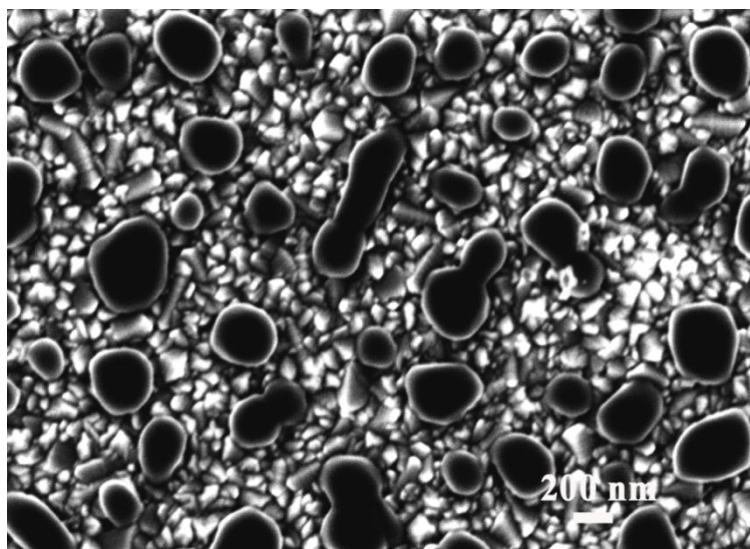


Figure S1. SEM images of BiVO₄.

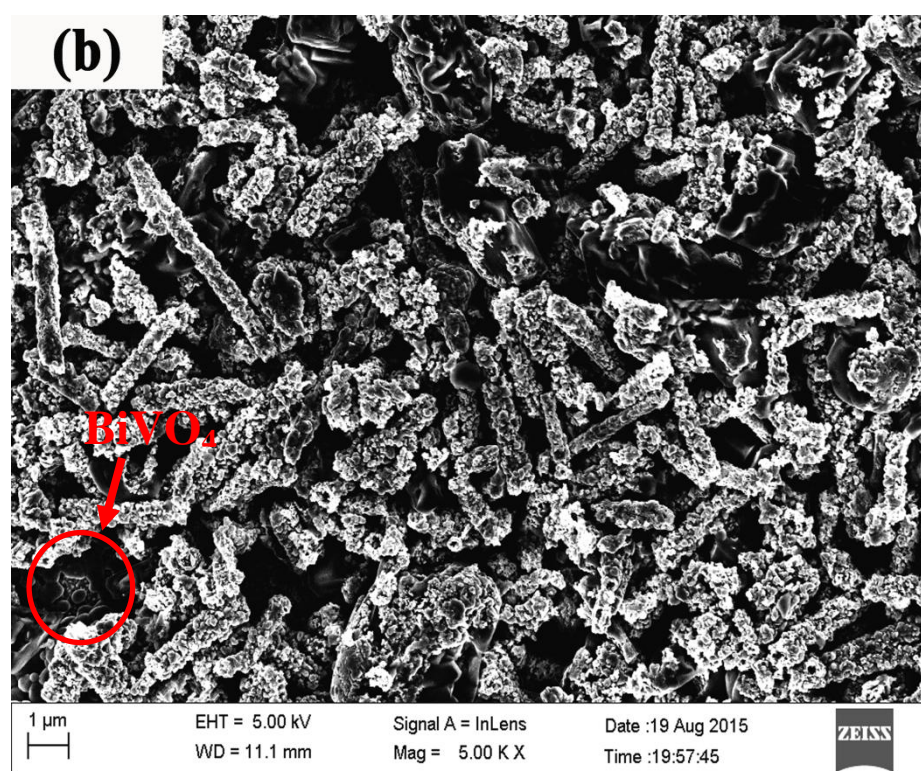
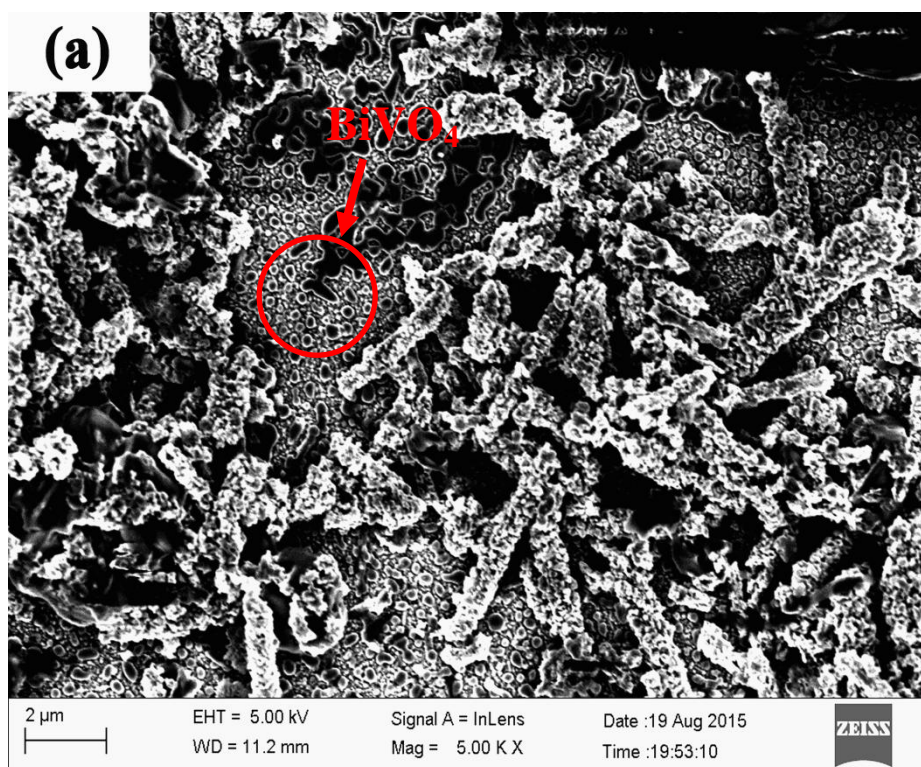


Figure S2. SEM images of AB-40.

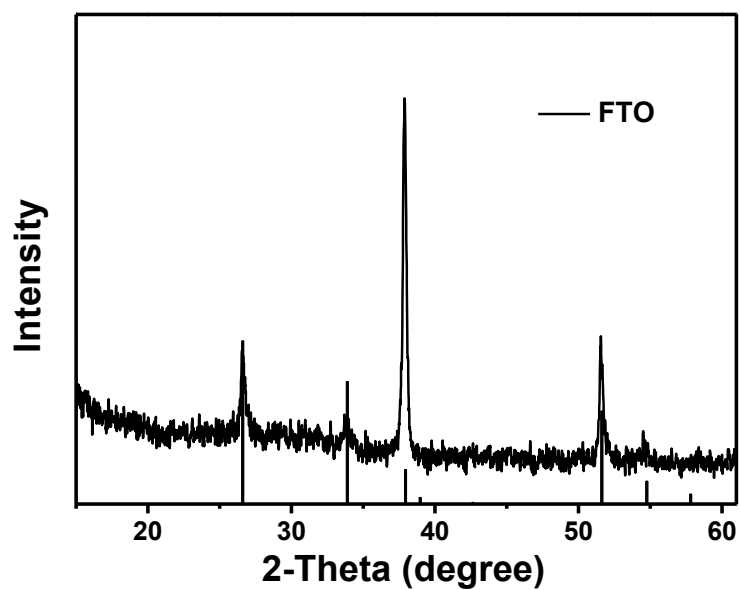


Figure S3. XRD pattern of FTO (JCPDS No. 41-1445).

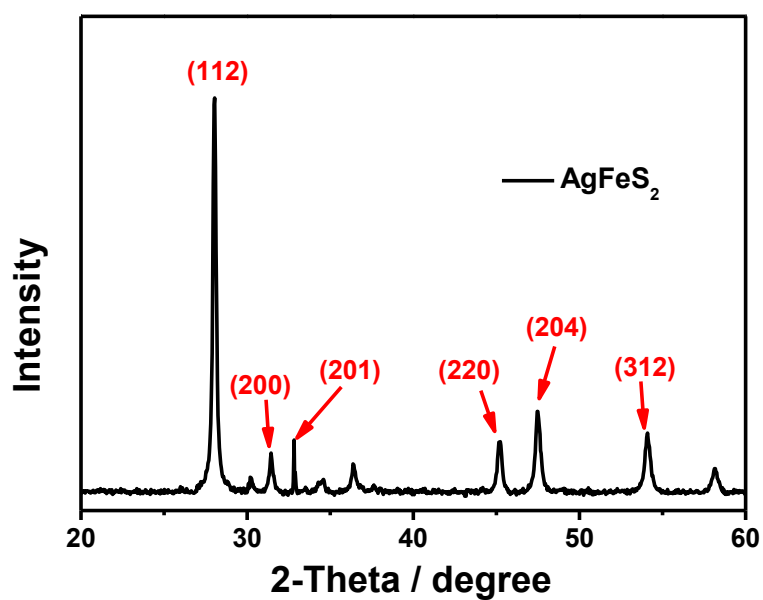


Figure S4. XRD pattern of AgFeS₂ (JCPDS No. 48-1895).

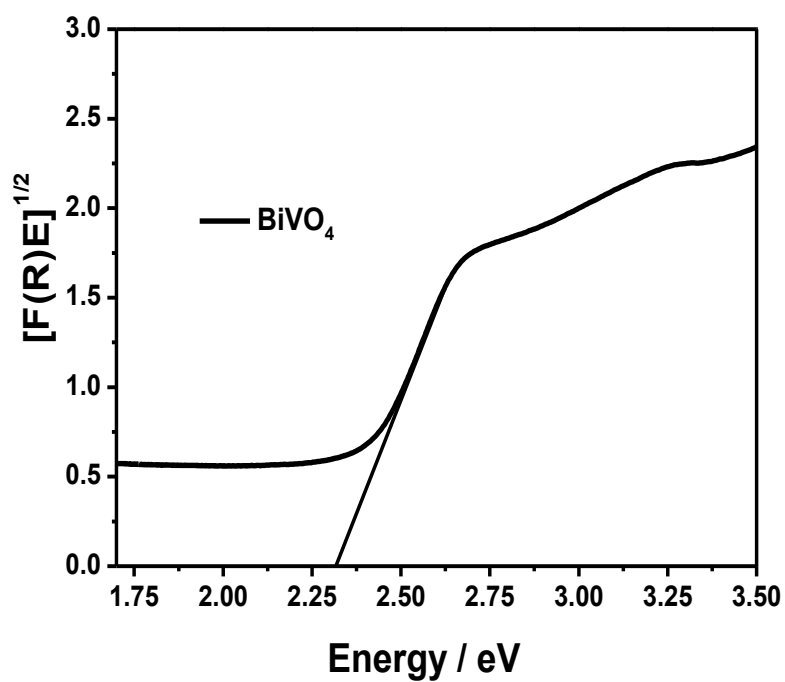


Figure S5. Optical band gap energy (E_g) of BiVO_4 .

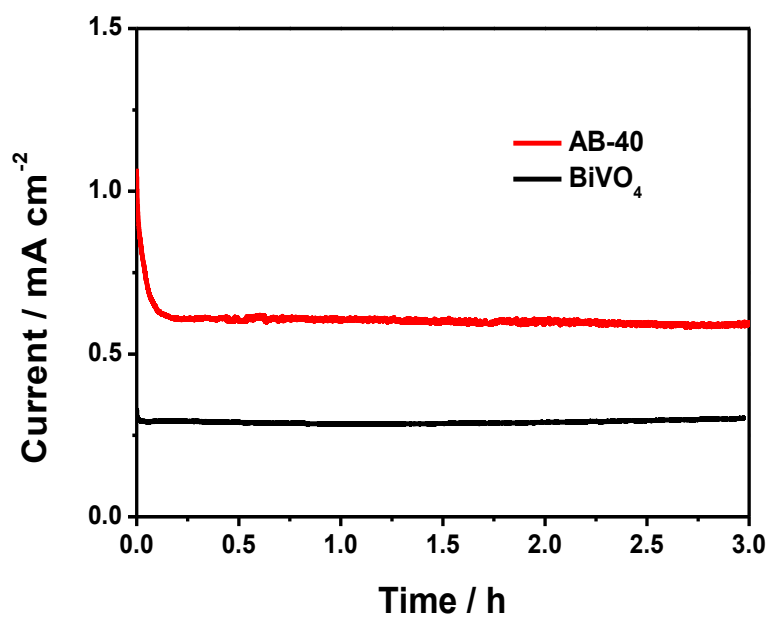


Figure S6. Current density vs time for AB-40 electrode at an applied potential of 1.6 V (vs Ag/AgCl) under AM 1.5 G illuminations (100 mW/cm^2).

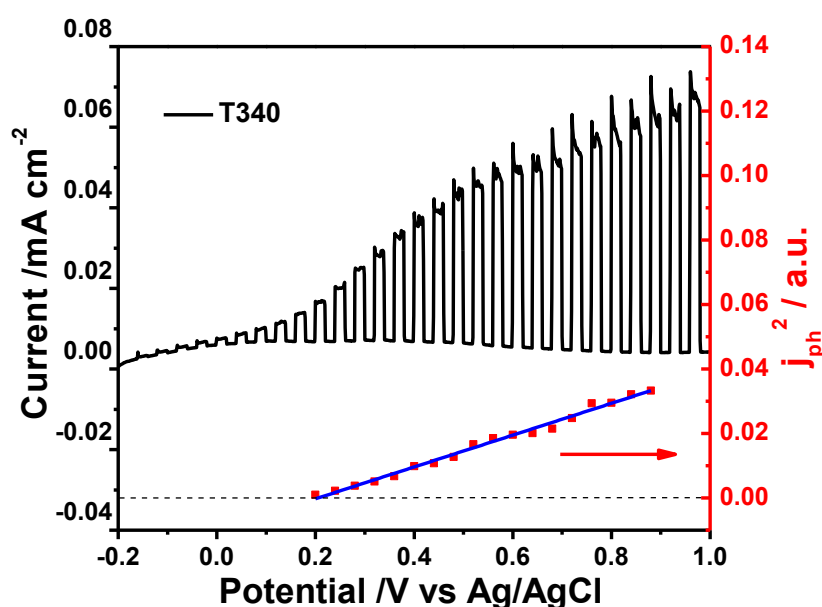


Figure S7. E_{FB} measurements of BiVO_4 by the photocurrent (j_{ph}) onset method using the fit to Butler theory for j_{ph}^2 in the mixture of the electrolyte of 1 mol/L Na_2SO_4 and 1 mol/L AcOK under simulated solar light illumination (a scan rate of 1 mV/s, scanned from positive side, and a light intensity of 100 mW/cm²).

The position of the semiconductor band is an important physical property of the semiconductor. Herein, the flat band potential (E_{FB}) is measured using the photocurrent onset potential for BiVO_4 film.^[S1] Typically, when the surface of the semiconductor electrode and the solution interface are contacted, the surface band bends to form a built-in electric field. According to the mechanism of photocurrent, photo-generated electrons migrate to form the photocurrent in the effect of built-in electric field. When a reverse bias is applied, it can offset the part of the built-in electric field. As the built-in voltage approaches zero, the current is zero, and the external voltage at this time is equal to the flat band. Therefore, ignoring the deviation of the flat band and the conduction band potential, it can be considered that the position of the conduction band is approximated by the position of the flat band potential.

E_{FB} is measured using the photocurrent onset potential for BiVO_4 film in aqueous solution. Figure 10 shows the photocurrent of BiVO_4 film in a mixture of the electrolyte of 1 mol/L

Na₂SO₄ and 1 mol/L AcOK with simulated solar light (100 mW/cm²). By alternating light and dark measures of linear sweep photovoltammetry, a step change could be measured by photocurrent density (j_{ph}) with the scan. From the onset of j_{ph} , the Buttler method is used to calculate E_{FB} using equation ($j_{ph}^2 \sim (E - E_{FB})$), where j_{ph}^2 is proportional to potential E .^[S1, S2] The square of the j_{ph} vs. E would have an x intercept of E_{FB} . As shown in Figure S7, E_{FB} of BiVO₄ is 0.20 eV vs. Ag/AgCl. To further calculate, it is 0.40 eV vs. NHE. Thereby, E_{CB} of BiVO₄ is about 0.40 eV. As the band gap for BiVO₄ is evaluated as 2.32 eV from the UV-vis spectrum, according to the formula $E_g = E_{VB} - E_{CB}$, the corresponding valence band potentials for BiVO₄ film is about 2.7 eV. Therefore, the value of E_{CB} measured by photocurrent onset potential is accorded with the calculated result.

Reference:

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